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(54) **SRAM core cell for light-emitting display**

(57) A SRAM core cell for a light-emitting display applicable to a data driver of an organic electro-luminescence light-emitting display device includes thin film transistors as a data memory for a data driver of the light-emitting display. The SRAM core cell also includes switching transistors and data memory transistors. The switching transistors are coupled to a bit line and a word line to select data writing or reading. The data memory transistors are coupled to a power voltage or a ground voltage to enable data writing and reading. The bit line and the word line are formed in first and second directions. The channels of the switching transistors and the data memory transistors are formed in an oblique direction with respect to the first and second directions.

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